

## EAST Search History

## EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	3054	(257/59,72).CQLS	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/07 15:27
S2	2804	S1 and (gate or drain or source)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/04 12:32
S3	2143	S1 and (channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/04 12:32
S4	353	S1 and ("metal oxide")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/04 12:33
S5	45	S1 and (channel near3 composition)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/04 13:32
S6	34	S5 and (gallium or Ga) and (Germanium or Ge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/04 12:50
S7	3	S5 and (Ga and Ge and Pb and Sn and In)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/04 12:50
S8	7	(channel near3 composition) and (metal near4 oxide) and (Ga and Ge and Pb and Sn and In)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/04 13:35
S9	0	(channel near3 composition) with (Ga and Ge and Pb and Sn and In)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/04 13:35
S10	3	(channel near3 composition) and (metal near4 oxide) and (channel with (Ga and Ge and Pb and Sn and In))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/04 14:58
S11	1355	(257/43,613,616,e29.068,e29.079,e29.080,e29.100,e29.103).CQLS	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/04 14:59

S13	789	S11 and (body or substrate or channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/04 14:59
S14	250	(body or substrate or channel) with ((gallium or ga) and (germanium or ge) and (lead or pb) and (tin or sn) and (indium or in))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 08:03
S15	1	S13 and S14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/04 15:04
S16	170	(body or substrate or channel) with ((gallium or ga) same (germanium or ge) same (lead or pb) same (tin or sn) same (indium or in))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 08:02
S17	19	S16 and transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/04 15:11
S18	69	S16 and (transistor or gate or drain or source)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 08:02
S19	63	S18 and (@ad<"20040312" or @rlad<"20040312")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 08:04
S20	5245	((gallium or ga) same (germanium or ge) same (lead or pb) same (tin or sn) same (indium or in))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 08:05
S21	2308	S20 and (transistor or gate or drain or source)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 08:05
S23	170	(body or substrate or channel) with ((gallium or ga) same (germanium or ge) same (lead or pb) same (tin or sn) same (indium or in))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 08:02
S24	69	S23 and (transistor or gate or drain or source)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 08:02
S25	2239	S21 not S24	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 08:05
S26	1561	S25 and (body or substrate or channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 08:05

S27	1443	S26 and (@ad<"20040312" or @rlad<"20040312")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 08:06
S28	1071	((gallium or ga) same (germanium or ge) same (lead or pb) same (tin or sn) same (indium or in)) with oxide\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/14 09:38
S29	522	S28 and (transistor or gate or drain or source)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 08:05
S30	505	S29 not S24	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 08:05
S31	361	S30 and (body or substrate or channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 08:05
S32	321	S31 and (@ad<"20040312" or @rlad<"20040312")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 09:55
S33	104092	semiconduct\$5 near3 oxid\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 09:18
S34	88922	semiconduct\$5 near2 oxid\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 09:38
S35	28	S34 and S32	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 09:21
S36	7689	S34 and ((switch\$4 or (turn near2 on)) near4 (speed or time))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 09:39
S37	1	S36 and S32	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 09:22
S38	7128	S36 and (gate or drain or source)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 09:39
S40	6956	S38 and ((gallium or ga) or (germanium or ge) or (lead or pb) or (tin or sn) or (indium or in))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 09:39

S41	36150	S34 same (body or substrate or channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 09:38
S42	2977	S41 and ((switch\$4 or (turn near2 on)) near4 (speed or time))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 09:39
S43	2782	S42 and (gate or drain or source)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 09:39
S44	2730	S43 and ((gallium or ga) or (germanium or ge) or (lead or pb) or (tin or sn) or (indium or in))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 09:41
S45	458	S44 and (thin adj film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 09:41
S46	1235	S43 and ((gallium or ga) or (germanium or ge) or (lead or pb) or (tin or sn) or (indium))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 09:45
S47	323	S46 and (thin adj film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 09:41
S48	361	"semiconducting metal oxide" or "semiconducting metal oxides"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 09:54
S49	162	S48 and (gate or drain or source)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 09:54
S50	155	S49 and (@ad<"20040312" or @rlad<"20040312")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 09:55
S51	641	(257/43).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 10:26
S52	156	S51 and (gate or drain or source)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 10:26
S53	40	S51 and (gate or drain or source) and channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 10:37

S54	10	("20030047785"   "20030111663"   "20030218221"   "20030218222"   "5744864").PN.	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 10:37
S55	7	("4733284"   "4900370"   "5229644"   "5397920"   "5619044").PN. OR ("5744864").URPN.	US-PGRUB; USPAT; USOCR	OR	OFF	2006/01/05 12:17
S56	22008	amorphous with oxide	US-PGRUB; USPAT; USOCR	OR	OFF	2006/01/05 12:28
S58	5466	S56 and (drain and gate and source)	US-PGRUB; USPAT; USOCR	OR	OFF	2006/01/05 12:29
S60	3548	S58 and (thin adj film)	US-PGRUB; USPAT; USOCR	OR	OFF	2006/01/05 12:29
S61	8826	amorphous near3 oxide	US-PGRUB; USPAT; USOCR	OR	OFF	2006/01/05 12:30
S62	1953	S61 and (drain and gate and source)	US-PGRUB; USPAT; USOCR	OR	OFF	2006/01/05 12:42
S63	1313	S62 and (thin adj film)	US-PGRUB; USPAT; USOCR	OR	OFF	2006/01/05 12:30
S64	1109	S63 and channel	US-PGRUB; USPAT; USOCR	OR	OFF	2006/01/05 12:41
S65	59	(amorphous near3 oxide) with channel	US-PGRUB; USPAT; USOCR	OR	OFF	2006/01/05 12:32
S66	77	(amorphous near3 oxide) with (purpose)	US-PGRUB; USPAT; USOCR	OR	OFF	2006/01/05 12:32
S67	992	S63 and (sputter or sputtering)	US-PGRUB; USPAT; USOCR	OR	OFF	2006/01/05 12:42
S68	227	S61 with (sputter or sputtering)	US-PGRUB; USPAT; USOCR	OR	OFF	2006/01/05 12:42
S69	90	S68 and (drain and gate and source)	US-PGRUB; USPAT; USOCR	OR	OFF	2006/01/05 12:42
S70	1	channel with (ternary adj oxide)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/07 07:46
S71	11	semiconductor with (ternary adj oxide)	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/07 08:30
S72	1	semiconductor and ((ternary adj oxide) with ((Ga or In) and (Ge or Sn or Pb)))	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/07 07:51
S73	6	((ternary adj oxide) with ((Ga or In) and (Ge or Sn or Pb)))	US-PGRUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/07 07:56

S74	9	("4733284"   "4900370"   "5229644"   "5397920"   "5619044").PN. OR ("5744864").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/04/07 08:17
S75	12	(ternary adj oxide) and mobility	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/07 08:33
S76	872	channel with mobility with oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/07 08:34
S77	222	channel with mobility with oxide with metal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 09:11
S78	3223	oxide with mobility	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 09:21
S79	21	(257/e29.068).CQLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/04/07 09:21
S80	4280	amorphous with (metal adj oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/07 11:15
S81	1160	amorphous near2 (metal adj oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/07 11:16
S82	560	amorphous adj (metal adj oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/07 12:05
S83	178	S82 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/07 12:10
S84	1	(pulsed adj laser adj deposition) with (amorphous with (metal adj oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/07 12:22
S85	226	jow.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/07 12:37
S86	1	S85 and (pulsed adj laser adj deposition)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/07 12:22
S87	1	60-198861A	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/07 12:40
S88	9	("4733284"   "4900370"   "5229644"   "5397920"   "5619044").PN. OR ("5744864").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/04/07 12:37
S89	158	"SnO.sub.2" with amorphous with form\$5	US-PGPUB; USPAT; EPO; JPO;	OR	ON	2006/04/07 12:42

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S90	0	"SnO.sub.2" with amorphous with (pulsed adj laser adj deposition)	US-PGRUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/07 12:41
S91	0	"SnO.sub.2" with amorphous with pld	US-PGRUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/07 12:41
S92	2	"SnO.sub.2" with amorphous with form\$5 and (pld or (pulsed adj laser))	US-PGRUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/07 12:43
S93	115	"SnO.sub.2" and (pld or (pulsed adj laser adj deposition))	US-PGRUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/07 12:52
S94	59	"SnO.sub.2" and (pld or (pulsed adj laser adj deposition)) and amorphous	US-PGRUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/07 12:43
S95	5	"SnO.sub.2" with (pld or (pulsed adj laser adj deposition))	US-PGRUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/07 13:52
S96	16	oxide with (pld or (pulsed adj laser adj deposition)) with amorphous	US-PGRUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/07 13:21
S97	4280	(metal adj oxide) with amorphous	US-PGRUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/07 13:21
S98	1541	(metal adj oxide) with amorphous with form\$4	US-PGRUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/07 13:22
S99	506	(metal adj oxide) with amorphous with form\$4 and semiconductor	US-PGRUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/07 13:29
S100	8	("20030045038"   "20040241921"   "6432758"   "6555449").PN	US-PGRUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/07 13:26
S101	59	S99 and mobility	US-PGRUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/07 13:27
S102	11	S99 and (amorphous with mobility)	US-PGRUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/07 13:27
S103	105	(amorphous adj metal adj oxide) with form\$4 and semiconductor	US-PGRUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/07 13:31
S104	48	("ZnO" or "ZnO.sub.2") with (pld or (pulsed adj laser adj deposition))	US-PGRUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/07 13:52
S105	1	("ZnO" or "ZnO.sub.2") with amorphous with (pld or (pulsed adj laser adj deposition))	US-PGRUB; USPAT; EPO; JPO;	OR	ON	2006/04/07 13:52

S106	3190	(257/59,72).CQLS	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/07 15:28
S107	1317	(438/96,482).CQLS	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/07 15:29
S108	2952	(257/347).CQLS	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/04/14 09:37
S110	1947	(ITO with amorphous)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/14 09:57
S111	18	(ITO with amorphous) and (pulsed adj laser)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/14 09:57

**EAST Search History (Interference)**

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